PATENT ABSTRACTS OF JAPAN

(11)Publication number:

63-244748

(43) Date of publication of application: 12.10.1988

(51)Int.CI.

H01L 21/66 G01N 21/88

(21)Application number : 62-077796

(71)Applicant: FUJITSU LTD

(22)Date of filing:

31.03.1987

(72)Inventor: SUETAKE MIKIO

(54) CALIBRATION OF WAFER SURFACE INSPECTING DEVICE

(57)Abstract:

PURPOSE: To contrive so as not to be confused an adhered foreign substance with intentional foreign substances provided on a calibration wafer and to make it possible to prevent the lowering of the calibration accuracy even though the foreign substance is adhered on the wafer by a method wherein an antireflection film is provided on the surface of the substrate of the wafer. CONSTITUTION: An antireflection film 23, which consists of Si dioxide or Si nitride (SiN) and acts as reflection prevention to the wavelength of the incident

light of a wafer inspecting device, is formed on a

substrate 21, which consists of a clean Si wafer, of a calibration wafer and moreover, an Si nitride film or an Si dioxide film (The material is made to differ from that of the film 23.) formed thereon is patterned and a plurality of intendistributed sparsely, such as in the form of a 1-mm interval material.

the film 23.) formed thereon is patterned and a plurality of intentional foreign substances 22 distributed sparsely, such as in the form of a 1-mm interval matrix, are formed. The thickness of the film 23 is about 1000 & angst; in the film consisting of Si dioxide in case the wavelength of the incident light is 6330 & angst; (The light source is a helium-neon laser.) and is about 800 & angst; in the film consisting of Si nitride. When this calibration wafer is used, an adhered foreign substance adhered on the film 23 is detected very small than its actual size in a state to say that even a big foreign substance of 2 μ m, for example, is detected as a foreign substance of 0.4 μ m.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]